

This listing of claims will replace all prior versions, and listings, of claims in the application:

The Status of the Claims

1. (Cancelled)

2. (Currently Amended) A method for forming a contact hole or a via hole in a semiconductor device as defined in claim 1, further comprising:
applying, exposing and developing a photosensitive film on ~~the~~ a metal insulation film or ~~the~~ an interlayer insulation film to form a photosensitive film pattern on a region to contain the contact hole or the via hole; [[,]] and etching the metal insulation film or the interlayer insulation film using the photosensitive film pattern as a mask and using a plasma having spiral movement such that a top edge of the contact hole or the via hole is rounded simultaneously as the contact hole or the via hole is formed.

3. (Previously Presented) A method as defined in claim 2, wherein, etching the metal insulation film or the interlayer insulation film comprises using a gas of fluorine series as an etching gas.

4. (Currently Amended) A method as defined in claim [[+]] 2, further comprising:

after the contact hole or the via hole is formed, forming a barrier metal film on an inner wall of the contact hole or the via hole; and

filling the contact hole or the via hole with a metal material.

5. (Previously Presented) A method as defined in claim 4
wherein filling the contact hole or the via hole with the metal material
comprises forming the metal material on the barrier metal film.

6. (Previously Presented) A method as defined in claim 2,
further comprising:

after the contact hole or the via hole is formed, forming a barrier metal
film on an inner wall of the contact hole or the via hole; and
filling the contact hole or the via hole with a metal material.

7. (Previously Presented) A method as defined in claim 6
wherein filling the contact hole or the via hole with the metal material
comprises forming the metal material on the barrier metal film.

8. (Previously Presented) A method as defined in claim 3,
further comprising:

after the contact hole or the via hole is formed, forming a barrier metal
film on an inner wall of the contact hole or the via hole; and
filling the contact hole or the via hole with a metal material.

9. (Previously Presented) A method as defined in claim 8
wherein filling the contact hole or the via hole with the metal material

comprises forming the metal material on the barrier metal film.